20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A. TELEPHONE: (973) 376-2922

Mechanical Qutline

2N1038, 2N1039*, 2N1040, 2N1041* A 2N2552, 2N2553*, 2N2554, 2N2555* B 2N2556, 2N2557*, 2N2558, 2N2559* C

Available to Military Specifications

PNP GERMANIUM ALLOY JUNCTION POWER TRANSISTORS

These hermetically sealed and dynamically tested units are designed to switch reactive and resistive loads at maximum efficiency by using a unique internal heat-sink design. Each unit can dissipate up to .4 watt in free air at 25°C and up to 1 watt in forced air at 25°C and can also be pressed into suitable heat-sink wells to dissipate up to 8 watts at 71°C. Typical applications include relay drivers, pulse amplifiers, audio amplifiers and high current switching circuits. The collector lead is internally connected to the case.

MAXIMUM DESIGN LIMITS

	2N1038 2N2552 2N2556	2N1039 2N2553 2N2557	2N1040 2N2554 2N2558	2N1041 2N2555 2N2559	Units
Collector-to-Base Voltage, V _{CB}	-40	-60	80	-100	Volts
Collector-to-Emitter Voltage, V _{CE} Acting Region Emitter Forward Biased Cutoff Region Emitter Reverse Biased	-30 -40	40 60	-50 -80	-60 -100	Volts Volts
Emitter-to-Base Voltage, V _{EB}		-20			Volts
Collector Current, Ic		-3.0			Amp
Base Current, I _B		-1.0			Amp
Operating and Junction Temp. T _J		– 55	to +100		°C
Thermal Resistance, Junction to Free Air Θ JA		185			°C/W
Thermal Resistance, Junction to Case ⊕ JC		3.67			°C/W

CHARACTERISTICS AT 25°C CASE TEMPERATURE

Parameter	Symbol	Condition	Min.	Max.	Units
Current Gain, Common Emitter	H _{FEI}	$V_{CE} = -0.5V, I_C = -1 A$	20	60	
Current Gain, Common Emitter	H _{FE2}	$V_{CE} = -0.5V$, $I_C = -50$ mA	33	200	
Base-to-Emitter Voltage	VBEI	$V_{CE} = -0.5V, I_C = -1.0 A$		-1.0	Volts
	YFEI		1.0		mhos
Base-to-Emitter Voltage	V _{BE2}	$V_{CE} = -0.5V$, $I_{C} = -50$ mA		-0.35	Volts
	Y _{FE2}		0.143		mhos
Collector-Emitter Saturation Voltage*	V _{CE} (sat)	$I_{\rm C} = -1$ A, $I_{\rm B} = -100$ and		0.25	Volts
Collector Junction Leakage Current	Iceo				
2N1038, 2N2552, 2N2556		$V_{C8} = -20V$			
2N1039, 2N2553, 2N2557		$V_{CB} = -30V$		-125	μAmp
2N1040, 2N2554, 2N2558		$V_{CB} = -40V$			
2N1041, 2N2555, 2N2559		$V_{CB} = -50V$			
Collector-Base Breakdown Voltage	BV _{CBO}	$I_{c} = -750$			
2N1038, 2N2552, 2N2556			40		
2N1039, 2N2553, 2N2557			-60		Volts
2N1040, 2N2554, 2N2558			-80		VUILS
2N1041, 2N2555, 2N2559			-100		
Collector Cutoff Current	I _{CEX}	$V_{BE} = +0.2V$			
2N1038, 2N2552, 2N2556		$V_{CE} = -40V$			
2N1039, 2N2553, 2N2557		$V_{CE} = -60V$		 650	μAmp
2N1040, 2N2554, 2N2558		$V_{CE} = -80V$			
2N1041, 2N2555, 2N2559		$V_{CE} = -100V$			

*Note: Measured adjacent to header to minimize lead effects.

my semi-Conductors